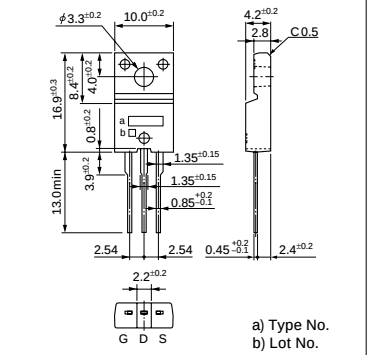
MOS FET FKV560 (under development)

Absolute Maximum Ratings (Ta=25ºC)

Symbol	Ratings	Unit
V_{DSS}	50	V
V_{GSS}	±20	V
I_D	±60	A
$I_{D\ (pulse)}$*	±180	A
P_D	40 (Tc=25ºC)	W
Tch	150	ºC
Tstg	–55 to +150	ºC

* $P_W \leqq 100\mu s$, duty ≦ 1%

Electrical Characteristics (Ta=25ºC)

Symbol	Test Conditions	Ratings min	Ratings typ	Ratings max	Unit
$V_{(BR)\ DSS}$	I_D = 100µA, V_{GS} = 0V	50			V
I_{GSS}	V_{GS} = +20V			+10	µA
	V_{GS} = –20V			–5	µA
I_{DSS}	V_{DS} = 50V, V_{GS} = 0V			100	µA
V_{TH}	V_{DS} = 10V, I_D = 250µA	1.3		2.3	V
$Re_{(yfs)}$	V_{DS} = 10V, I_D = 25A	20.0			S
$R_{DS\ (ON)}$	V_{GS} = 10V, I_D = 25A		9	11	mΩ
Ciss	V_{DS} = 10V, f = 1.0MHz, V_{GS} = 0V		2000		pF
Coss			1000		pF
Crss			150		pF
$t_{d\ (on)}$	I_D = 25A, V_{DD} ≒ 12V, R_L = 0.48Ω, V_{GS} = 10V		To be defined		ns
t_r					ns
$t_{d\ (off)}$					ns
t_f					ns
V_{SD}	I_{SD} = 50A, V_{GS} = 0V		1.0	1.5	V

External Dimensions FM20 (full-mold)